

# Fulvio Mazzamuto

## List of Publications by Year in descending order

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18  
papers

223  
citations

1307594

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h-index

1281871

11  
g-index

18  
all docs

18  
docs citations

18  
times ranked

239  
citing authors

#	ARTICLE	IF	CITATIONS
1	Extended Defects Formation in Nanosecond Laser-Annealed Ion Implanted Silicon. Nano Letters, 2014, 14, 1769-1775.	9.1	40
2	Doping of semiconductor devices by Laser Thermal Annealing. Materials Science in Semiconductor Processing, 2017, 62, 92-102.	4.0	40
3	Thermoelectric performance of disordered and nanostructured graphene ribbons using Greenâ€™s function method. Journal of Computational Electronics, 2012, 11, 67-77.	2.5	35
4	Bandgap nanoengineering of graphene tunnel diodes and tunnel transistors to control the negative differential resistance. Journal of Computational Electronics, 2013, 12, 85-93.	2.5	31
5	Segregation and activation of Ga in high Ge content SiGe by UV melt laser anneal. Journal of Applied Physics, 2019, 125, .	2.5	17
6	Solid phase recrystallization induced by multi-pulse nanosecond laser annealing. Applied Surface Science Advances, 2021, 3, 100053.	6.8	12
7	(Invited) Laser Thermal Annealing for Low Thermal Budget Applications: From Contact Formation to Material Modification. ECS Transactions, 2019, 89, 137-153.	0.5	7
8	Surface segregated Ga, In, and Al activation in high Ge content SiGe during UV melt laser induced non-equilibrium solidification. Japanese Journal of Applied Physics, 2019, 58, 120911.	1.5	7
9	Multilayered highly-active dopant distribution by UV nanosecond melt laser annealing in Ga and B co-implanted high Ge content SiGe:B epilayers. Japanese Journal of Applied Physics, 2020, 59, 050903.	1.5	7
10	Dopant Redistribution and Activation in Ga Ion-Implanted High Ge Content SiGe by Explosive Crystallization during UV Nanosecond Pulsed Laser Annealing. ECS Journal of Solid State Science and Technology, 2021, 10, 023005.	1.8	5
11	High energy excimer laser system for nanosecond annealing of semiconductor devices. , 2019, , .		5
12	Microsecond non-melt UV laser annealing for future 3D-stacked CMOS. Applied Physics Express, 2022, 15, 061002.	2.4	4
13	UV Excimer Laser Annealing for Next Generation Power Electronics. , 2016, , .		3
14	Super Activation of Highly Surface Segregated Dopants in High Ge Content SiGe Obtained by Melt UV Laser Annealing. , 2018, , .		3
15	UV nanosecond laser annealing for Ru interconnects. , 2020, , .		3
16	High performance polysilicon NEMS fabricated at low temperature with UV laser annealing. , 2016, , .		2
17	Defects Investigation in Nanosecond laser Annealed Crystalline Silicon: Identification and Localization. , 2018, , .		1
18	Solid Phase Recrystallization and Dopant Activation in Arsenic Ion-Implanted Silicon-On-Insulator by UV Laser Annealing. , 2021, , .		1